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KS54HCTLS 373 KS74HCTLS

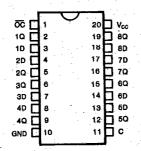
with 3-State Outputs

Octal D-Type Transparent Latches

FEATURES

- 8 latches in a single package
 Full parallel access for loading
- Function, pin-out, speed and drive compatibility with 54/74LS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current
- (I_{OL} = 24 mA @ V_{OL} = 0.5V) for direct bus interface • Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and
- military temperature ranges:
- KS74HCTLS: -40°C to +85°C
- KS54HCTLS: -55°C to +125°C Package options include plastic "small outline"
- packages, standard plastic and ceramic 300-mil DIPs

PIN CONFIGURATION



DESCRIPTION

The '373 consists of 8 high-speed D-type latches coupled to 3-state output buffers with high drive current capability. It can be used in implementing buffer registers, I/O ports, bidirectional bus drivers and working registers.

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The latches are transparent: when the enable (C) is high, the Q outputs follow the data (D) inputs. When the enable is low, the outputs latch at the levels that were set up at the D inputs.

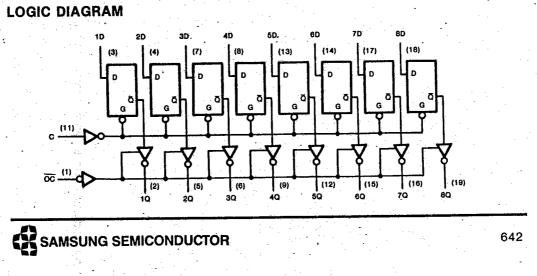
The output buffers are controlled by a common signal (\overline{OC}) which places the outputs at a high-impedance state when it is taken high. The \overline{OC} signal does not affect the internal operations of the latches. Old data can be retained or new data can be entered while outputs are off.

These devices provide speeds and drive capability equivalent to their LSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to Vcc and ground.

FUNCTION TABLE

, I	(Each	Latch)		
	Inputs		Output	
ŌC	Enable C	D	Q	
L	н	н	H	
L	Н	E.	L	
L	L T	· X	.Q ₀	
н	X	X	z	



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Absolute Maximum Ratings*

Supply Voltage Range Vcc. -0.5V to +7V DC Input Diode Current, I_{IK} (V_I < -0.5V or V_L > V_{CC} +0.5V) ±20 mA DC Output Diode Current, lox

 $(V_0 < -0.5V \text{ or } V_0 > V_{CC} + 0.5V) \dots \pm 20 \text{ mA}$

Continuous Output Current Per Pin, 1_0 (-0.5V < V₀ < V_{CC} +0.5V) \pm 70 mA Continuous Current Through

Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability. Power Dissipation temperature derating: Plastic Package (N): - 12mW/°C from 65°C to 85°C Ceramic Package (J): -12mW/°C from 100°C to 125°C

Octal D-Type Transparent Latches

with 3-State Outputs T-46-07-05

Recommended Operating Conditions

 Range
 KS74HCTLS:
 -40°C to
 +85°C

 KS54HCTLS:
 -55°C to
 +125°C

voltage level (either V_{CC} or GND)

Characteristic	Symbol	Test Conditions	T _A =25°C		KS74HCTLS $T_A = -40$ °C to $+85$ °C	KS54HCTLS T _A = -55°C to +125°C	Unit
			Тур		Guaranteed Lim	its	<u> </u>
Minimum High-Level Input Voltage	VIH			2.0	2.0	2,0	V
Maximum Low-Level Input Voltage	ViL		-	0.8	0.8	0.8	v
Minimum High-Level Output Voltage	Vон	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_0 = -20\mu A$ $I_0 = -6m A$	V _{CC} 4.2	V _{CC} -0,1 3.98	V _{CC} -0.1 3.84	V _{CC} -0.1 3.7	v
Maximum Low-Level Output Voltage	VoL	V _{IN} =V _{IH} or V _{IL} I _O =20µA I _O =12mA I _O =24mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	v
Maximum Input Current	lın	V _{IN} =V _{CC} or GND		±0.1	±1.0'	±1.0	μA
Maximum 3-State Leakage Current	loz	Output Enable =V _{IH} V _{OUT} =Vcc or GND		±0.5	±5.0	±10.0	μA
Maximum Quiescent Supply Current	lcc	V _{IN} =V _{CC} or GND I _{OUT} =0µA	-	8.0	80.0	160.0	μA
Additional Worst Case Supply Current	Δlcc	per input pin $V_Z=2.4V$ Other inputs: At V_{CC} or GND $I_O=0$		2.7	2.9	3.0	mA

DC ELECTRICAL CHARACTERISTICS (Vcc=5V±10% Unless Otherwise Specified)



AC	ELECTRICAL	CHARACTERISTICS (Input tr, tr<6 ns), HCTLS:	373

Characteristic	Symbol	Cendlilons		T _a = 25°C V _{CC} = 5.0V		K\$74HCTLS $\tilde{T}_{s} = -40^{\circ}C \text{ to } +85^{\circ}C$ $V_{CC} = 5.0V \pm 10\%$	KS54HCTLS $T_a = -55^{\circ}C \text{ to } +125^{\circ}C$ $V_{CC} = 5.0V \pm 10\%$	Unit
				Тур		Guarantee	d Limite	1.1
* Maximum Propagation Delay,	фин	CL= 50pF CL=150pF		14 17	18 21	23 28	27 33	ns
D to Q	t PHL	C _L =50pl C _L =150	14 17	18 21	23 28	27 33		
Maximum Propagation Delay, C to any Q	t PLH	C _L ≕50pF C _L ≕150pF		22 25	30 33	37 42	45 51	ns
	t PHL	C _L =50pl C _L =150		22 25	30 33	37 42	45 51	
Maximum Output Enable Time, OC to any Q	tpz _H	-BL=1kΩ	CL=50pF CL=150pF	24 27	32 35	40 45	48 54	- ns
	t _{PZL}		$C_L = 50 pF$ $C_L = 150 pF$	24 27	32 35	40 45	. 48 54	
Maximum Output Disable Time, OC to any Q	t _{PHZ}	R _L =1kΩ C _L =50p	19 19	25 25	31 31	37 37	ns	
Minimum Pulse Width, C High	ťw			6	10	12	15	ns
Minimum Setup Time, D before CI	tsu			2	3	4	5	ns
Minimum Hold Time, D after CI	th			6	10	12	15	ns
Maximum Input Capacitance	CiN			5				pF
Maximum Output Capacifance	COUT	Output D	isabled	10				pF
Power Dissipation Capacitance* (per latch)	CPD	OC=Vcc OC=GN	D	5 30				pF

* CPD determines the no-load dynamic power dissipation: PD=CPD Vcc² f + lcc Vcc. † For AC switching test circuits and timing waveforms see section 2.

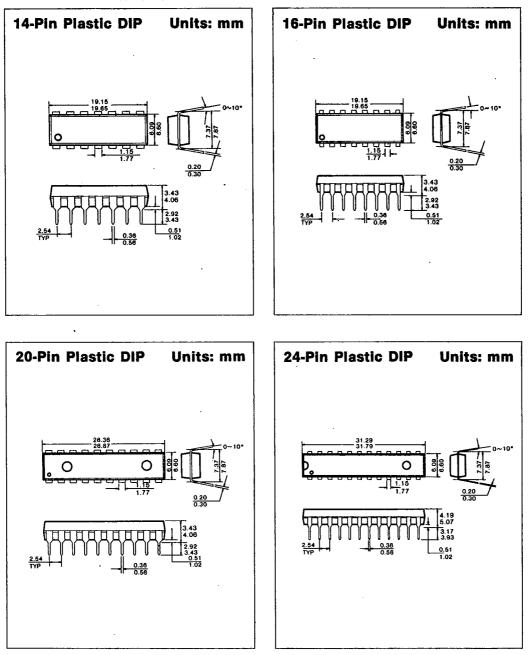
PACKAGE DIMENSIONS

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1. PLASTIC PACKAGES



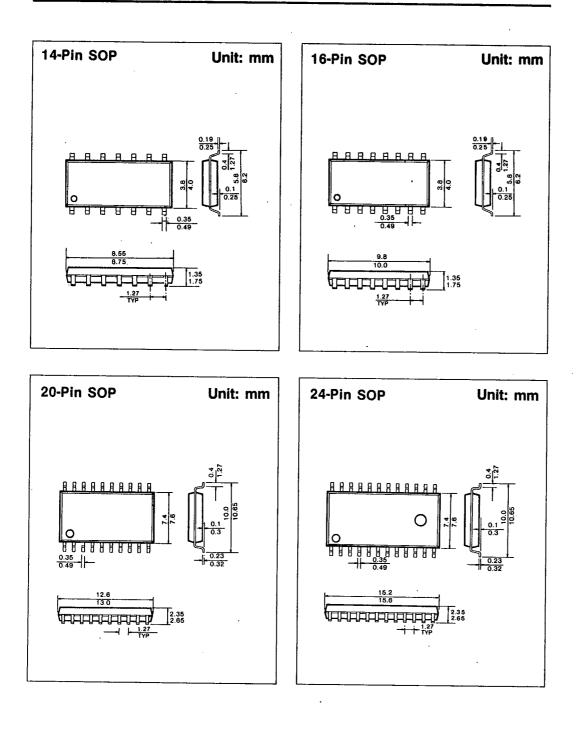
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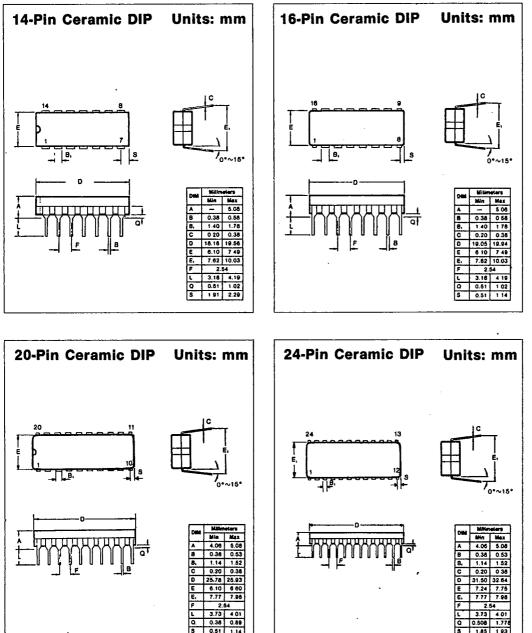
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2. CERAMIC PACKAGES



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